

## MOS Field Effect Transistor

## 2SJ205

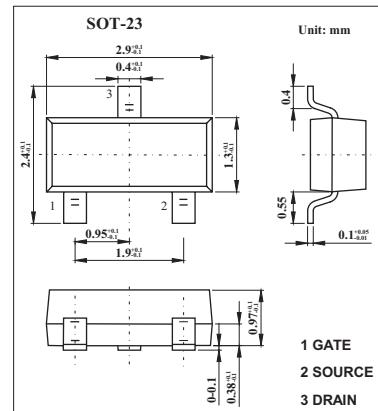
## ■ Features

- Directly driven by  $I_{GS}$  having a 3V power supply.

- Has low on-state resistance

$R_{DS(on)} = 5 \Omega$  MAX. @  $V_{GS} = -2.5V, I_D = -10mA$

$R_{DS(on)} = 3 \Omega$  MAX. @  $V_{GS} = -4V, I_D = -300mA$

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Drain to source voltage $V_{GS}=0$	$V_{DSS}$	-16	V
Gate to source voltage $V_{DS}=0$	$V_{GSS}$	$\pm 16$	V
Drain current (DC)	$I_D$	$\pm 500$	mA
Drain current(pulse) *	$I_D$	$\pm 1.0$	A
Power dissipation	$P_D$	2.0	W
Channel temperature	$T_{ch}$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ C$

\*  $PW \leq 10$  ms;  $d \leq 50\%$ .

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	$I_{DSS}$	$V_{DS}=-16V, V_{GS}=0$			-10	$\mu A$
Gate leakage current	$I_{GSS}$	$V_{GS}=\pm 16V, V_{DS}=0$			$\pm 5$	$\mu A$
Gate cut-off voltage	$V_{GS(off)}$	$V_{DS}=-5.0V, I_D=10 \mu A$	-1.4	-1.9	-2.4	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=-3.0V, I_D=0.3A$	0.4	0.5		s
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=-2.5V, I_D=10mA$		3.0	5.0	$\Omega$
		$V_{GS}=-4V, I_D=-0.3A$		1.5	3.0	$\Omega$
Input capacitance	$C_{iss}$	$V_{DS}=-3.0V, V_{GS}=0, f=1MHz$		105		pF
Output capacitance	$C_{oss}$			90		pF
Reverse transfer capacitance	$C_{rss}$			15		pF
Turn-on delay time	$t_{d(on)}$	$V_{GS(on)}=-3V, R_G=10 \Omega, V_{DD}=-3V, I_D=-0.3A, R_L=10 \Omega$		185		ns
Rise time	$t_r$			900		ns
Turn-off delay time	$t_{d(off)}$			40		ns
Fall time	$t_f$			135		ns

## ■ Marking

Marking	PD
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